

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S48	13	((714/718-723 365/200,201,189.01, 189.07).cccls.) and (non-volatile with memory with (self adj test or self-test))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 09:12
L2	24	((714/718-723 365/200,201,189.01, 189.07).cccls.) and (non-volatile with memory with (self adj test or self-test or BIST))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/28 09:12
S73	15	S72 not S71	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 17:06
S72	17	((stor\$3 writ\$3 transmit\$4 send\$3) near4 (BIST "built-in self-test" self-test (self adj test)) near4 (instruction or command or micro\$1code or configur\$5) same (tester ATE))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 17:06
S70	18	((stor\$3 writ\$3) near4 (BIST "built-in self-test" self-test (self adj test)) near3 (instruction or command or micro\$1code or configur\$5) same ((command control\$4) near2 (register unit block circuit)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 17:04
S71	12	S70 not S69	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 16:37
S69	6	(stor\$3 near3 (BIST or built\$1in\$1self\$1test or self\$1test) near3 (instruction or command or micro\$1code or configur\$5) same ((command control\$4) near2 (register unit block circuit)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 16:35
S68	1	((tester or ATE) and (stor\$3 near3 (BIST or built\$1in\$1self\$1test or self\$1test) near3 (instruction or command or micro\$1code or configur\$5) same ((command control\$4) near2 (register unit block circuit))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 15:53

S67	1	((tester or ATE) and (stor\$3 near3 (BIST or built\$1in\$1self\$1test or self\$1test) near3 (instruction or command or micro\$1code or configur\$5) near5 ((command control\$4) near2 (register unit block circuit))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 15:52
S66	1	((tester or ATE) same (stor\$3 near3 (BIST or built\$1in\$1self\$1test or self\$1test) near3 (instruction or command or micro\$1code or configur\$5) near5 ((command control\$4) near2 (register unit block circuit))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 15:46
S65	1	((tester or ATE) same (stor\$3 near3 (BIST or built\$1in\$1self\$1test or self\$1test) near3 (instruction or command or micro\$1code or configur\$5) near5 ((command control\$4) near2 (register unit block circuit))) and (non\$1volatile near2 memory or flash or EPROM or EEPROM or NVRAM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 15:44
S25	22	((tester or ATE) same (BIST or built\$1in\$1self\$1test or self\$1test) near6 (instruction or command or micro\$1code or configur\$5) and (non\$1volatile near2 memory or flash or EPROM or EEPROM or NVRAM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 15:25
S63	108	((BIST "built-in self-test" self-test (self adj test)) near4 (instruction command)) near5 data	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 15:23
S61	3621	S60 near5 (instruction command) near6 data	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/08 15:18
S64	3	S60 near4 S63	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 18:42
S55	32	((read\$3 writ\$3 stor\$3) near4 (BIST "built-in self-test" self-test (self adj test)) near4 (instruction command)) and (non-volatile "non volatile" FLASH EEPROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 18:41

S62	141	(714/718-723,733,734 365/200, 201,189.01,189.07).cccls. and S61	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 18:34
S50	13368	((714/718-723 365/200,201,189.01, 189.07).cccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 18:34
S60	382321	(non-volatile "non volatile" FLASH EEPROM NVRAM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 18:32
S59	1	"5640509".PN.	USPAT; USOCR	OR	ON	2004/12/20 17:16
S58	1	"5668816".PN.	USPAT; USOCR	OR	ON	2004/12/20 17:16
S57	1	"5802071".PN.	USPAT; USOCR	OR	ON	2004/12/20 17:15
S56	7	S52 and S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 17:11
S53	6	((read\$3 writ\$3 stor\$3) near4 (BIST "built-in self-test" self-test (self adj test)) near4 (instruction command)) same (non-volatile "non volatile" FLASH EEPROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 17:09
S54	0	S52 and S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 17:06
S49	30	((read\$3 writ\$3 stor\$3) near4 (BIST "built-in self-test" self-test (self adj test)) near4 (instruction command)) same (non-volatile "non volatile" FLASH \$3ROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 17:04
S52	971	(714/733,734).cccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 17:03
S51	13	S50 and S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 14:17

S47	8	((read\$3 near4 (BIST "built-in self-test" self-test) near4 (instruction command)) same (non-volatile "non volatile" FLASH \$3ROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 14:14
S41	8	((365/201,189.01,189.07).ccls.) and (non-volatile with memory with (self adj test or self-test))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 13:56
S46	7	((read\$3 near4 (BIST or built\$1in\$1self\$1test or self\$1test) near4 (instruction or micro\$1code)) and (non-volatile "non volatile" FLASH \$3ROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 13:49
S44	2	((read\$3 near4 (BIST or built\$1in\$1self\$1test or self\$1test) near4 (instruction or micro\$1code) same (cell or array)) and (non-volatile "non volatile" FLASH \$3ROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 13:47
S45	2	S43 and S44	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 13:27
S43	8	((stor\$3 writ\$3) near4 (BIST or built\$1in\$1self\$1test or self\$1test) near4 (instruction or micro\$1code) same (cell or array)) and (non-volatile "non volatile" FLASH \$3ROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 13:25
S30	3	((stor\$3 writ\$3) near6 (BIST or built\$1in\$1self\$1test or self\$1test) near6 (instruction or micro\$1code) same (cell or array)) and (non\$1volatile or FLASH or EEPROM)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/20 13:10
S42	2	"5640354".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 11:14
S36	2	"5410544".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 11:14

S8	120	Non-volatile with memory with (self adj test or self-test)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 10:07
S40	6830	(365/201,189.01,189.07).ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 10:06
S39	2	"6473346".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 10:05
S37	86	((non\$1volatile FLASH) with tester).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/11 09:27
S38	0	"20030164510".URPN.	USPAT	OR	ON	2004/06/10 18:55
S34	36	((non\$1volatile FLASH) with tester).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 18:51
S35	6	("4495567"   "4969148"   "5016212"   "5212776"   "5245572"   "5297148").PN.	USPAT	OR	ON	2004/06/10 18:32
S33	47	(FLASH with tester).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 18:31
S32	2	((stor\$3 writ\$3) near4 (BIST or built\$1in\$1self\$1test or self\$1test) near4 (instruction or micro\$1code) same (cell or array)) and (non\$1volatile or FLASH or EEPROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 18:30
S31	3	((stor\$3 writ\$3) near6 (BIST or built\$1in\$1self\$1test or self\$1test) near6 (instruction or micro\$1code) same (cell or array)) and (non\$1volatile or FLASH or EEPROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 18:09
S27	11	((stor\$3 writ\$3) near6 (BIST or built\$1in\$1self\$1test or self\$1test) near6 (instruction or micro\$1code) same (cell or array) same (memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 18:04

S29	2	(( NON\$1VOLATILE) same (MEMORY DEVICE EEPROM FLASH) and (CONTROL near2 CIRCUIT) and COMPARATOR and (COMPARE near4 DATA) with (PREDEFINED near4 DATA) and (SELF\$1TEST near6 INSTRUCTION))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 17:09
S28	2	(( NON\$1VOLATILE) same (MEMORY DEVICE EEPROM) and (CONTROL near2 CIRCUIT) and COMPARATOR and (DETECT near4 DEFECT\$3 near4 MEMORY near4 CELL) same (COMPARE near4 DATA) with (PREDEFINED near4 DATA) and (SELF\$1TEST near6 INSTRUCTION))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 17:08
S26	1	((stor\$3 writ\$3) near6 (BIST or built\$1in\$1self\$1test or self\$1test) near6 (instruction or micro\$1code or configur\$5) same (first near4 array) same (second near4 array))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 16:41
S24	8	( ((tester or ATE) same (instruction or command or micro\$1code or configur\$5) and (non\$1volatile or flash or EEPROM or NVRAM) and (BIST or built\$1in\$1self\$1test or self\$1test))) and (test\$3 same decod\$3 same address near2 buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 13:21
S23	202	((tester or ATE) same (instruction or command or micro\$1code or configur\$5) and (non\$1volatile or flash or EEPROM or NVRAM) and (BIST or built\$1in\$1self\$1test or self\$1test))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 13:21
S21	104	((external near4 tester or ATE) same (instruction or command or micro\$1code or configur\$5) and (non\$1volatile near2 memory or flash or \$2ROM) and (BIST or built\$1in\$1self\$1test or self\$1test))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/10 12:24
S22	4	(non\$1volatile or flash) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/09 12:35
S20	231	((external near4 tester or ATE) same (instruction or command or micro\$1code or configur\$5) and (non\$1volatile near2 memory or flash or \$2ROM) and (BIST or built or self))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 16:39

S19	140	((external near4 tester) same (instruction or command or micro\$1code or configur\$5) and (non\$1volatile near2 memory or flash or \$2ROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 16:34
S17	372	((external near4 tester or ATE) same (instruction or command or micro\$1code or configur\$5) and (non\$1volatile near2 memory or flash or \$2ROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 16:34
S18	3	( ((external near4 tester or ATE) same (instruction or command or micro\$1code or configur\$5) and (non\$1volatile near2 memory or flash or \$2ROM))) and (compar\$4 same control same decod\$3 same (BIST or built or self))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:53
S16	129	( ((external near4 tester) same (instruction or command or micro\$1code or configur\$5) and (non\$1volatile near2 memory or flash or \$2ROM))) not ((non\$1volatile or flash) with (self or built or bist) and decod\$3 and mode and address near2 buffer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:47
S1	276	(non\$1volatile or flash) with (self or built or bist) and decod\$3 and mode and address near2 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:46
S11	93	((external near4 tester) same (instruction or command or micro-code or micro near2 code) and (non\$1volatile near2 memory or flash or \$2ROM))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:43
S15	9	(( ((external near4 tester) same (instruction or command or micro-code or micro near2 code) and (non\$1volatile near2 memory or flash or \$2ROM))) and (stor\$3 or writ\$3 or receiv\$3) near4 self\$1test)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:39
S14	0	( ((external near4 tester) same (instruction or command or micro-code or micro near2 code) and (non\$1volatile near2 memory or flash or \$2ROM))) and sef\$1test	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:39
S13	0	(( ((external near4 tester) same (instruction or command or micro-code or micro near2 code) and (non\$1volatile near2 memory or flash or \$2ROM))) and (stor\$3 or writ\$3 or receiv\$3) same sef\$1test)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:39

S12	0	(( ((external near4 tester) same (instruction or command or micro-code or micro near2 code) and (non\$1volatile near2 memory or flash or \$2ROM))) and (stor\$3 or writ\$3 or receiv\$3) near4 sef\$1test)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:39
S10	3	(Non-volatile with memory with (self adj test or self-test)) and (external near4 tester) same (instruction or command or micro-code or micro near2 code) and (non\$1volatile or flash or EPROM or ROM)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:31
S9	6	(Non-volatile with memory with (self adj test or self-test)) and tester same (instruction or command)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 14:28
S7	13	((non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer) and (array or matrix) same (non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer) and (instruct\$3 command)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 12:50
S4	17	((non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer) and (array or matrix) same (non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 12:49



S6	4	(((((non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer) and (array or matrix) same (non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer) and (array or matrix) same cell same control same (non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer) not ((non\$1volatile or flash) with (self or built or bist) same decod\$3 same mode same address near2 buffer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 12:48
S5	8	(((((non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer) and (array or matrix) same (non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer) and (array or matrix) same cell same control same (non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 12:41
S3	19	(non\$1volatile or flash or memory) with (self or built or bist) with test\$3 same decod\$3 same mode same address near2 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 12:38
S2	7	(non\$1volatile or flash) with (self or built or bist) same decod\$3 same mode same address near2 buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/08 12:36